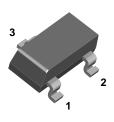




MMBD1501/A / 1503/A / 1504/A / 1505/A

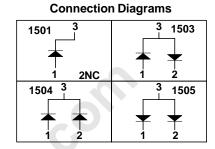


11 MARKING

SOT-23

MMBD1501 11 MMBD1501A A11 MMBD1503 13 MMBD1503A A13 MMBD1504A A14 MMBD1504 14 MMBD1505 15 MMBD1505A A15

3



Small Signal Diodes

Absolute Maximum Ratings* T₄ = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|--------------------|--|-------------|--------|
| V_{RRM} | Maximum Repetitive Reverse Voltage | 200 | V |
| I _{F(AV)} | Average Rectified Forward Current | 200 | mA |
| I _{FSM} | Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond | 1.0 2.0 | A A |
| T _{stg} | Storage Temperature Range | -55 to +150 | °C |
| T _J | Operating Junction Temperature | 150 | °C |

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

| Symbol | Parameter | Value | Units |
|-----------------|---|-------|-------|
| P_{D} | Power Dissipation | 350 | mW |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 357 | °C/W |

Electrical Characteristics T_A = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|----------------|-------------------|---|--|---|--------------------------|
| V_R | Breakdown Voltage | $I_R = 5.0 \mu A$ | 200 | | V |
| V _F | Forward Voltage | $I_F = 1.0 \text{ mA}$ $I_F = 10 \text{ mA}$ $I_F = 50 \text{ mA}$ $I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$ $I_F = 300 \text{ mA}$ | 620 720 800 830 0.87 0.90 | 720 830 890 930 1.1 1.15 | mV mV mV V V |
| I _R | Reverse Current | $V_R = 125 \text{ V}$ $V_R = 125 \text{ V}, T_A = 150 ^{\circ}\text{C}$ $V_R = 180 \text{ V}$ $V_R = 180 \text{ V}, T_A = 150 ^{\circ}\text{C}$ | | 1.0 3.0 10 5.0 | nA μA nA μA |
| Ст | Total Capacitance | $V_R = 0$, $f = 1.0 \text{ MHz}$ | | 4.0 | PF |

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations



Small Signal Diode

(continued)

Typical Characteristics

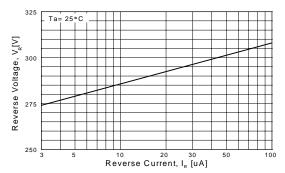


Figure 1. Reverse Voltage vs Reverse Current BV - 3.0 to 100 uA

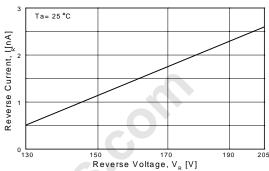


Figure 2. Reverse Current vs Reverse Voltage IR - 130 - 250 Volts

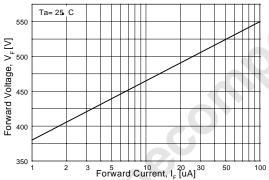


Figure 3. Forward Voltage vs Forward Current VF - 1 to 100 uA

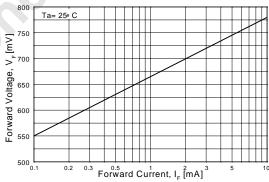


Figure 4. Forward Voltage vs Forward Current VF - 0.1 to 10 mA

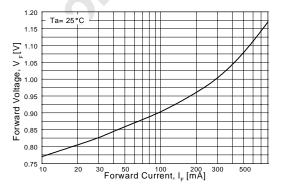


Figure 5. Forward Voltage vs Forward Current VF - 10 to 800 mA

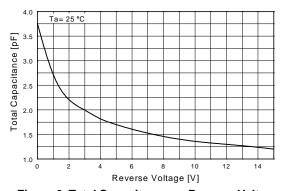


Figure 6. Total Capacitance vs Reverse Voltage VR - 0 to 15 V



Small Signal Diode

(continued)

Typical Characteristics (continued)

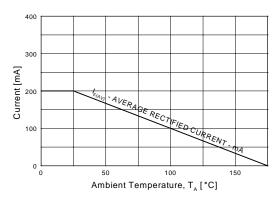


Figure 7. Average Rectified Current ($I_{F(AV)}$) versus Ambient Temperature (T_A)

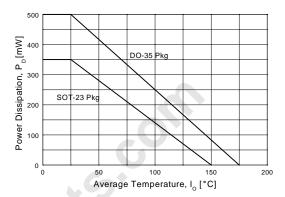


Figure 8. Power Derating Curve



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| The Power Franch | nise™ | OPTOLOGIC® | SILENT SWITCHER® | VCX™ |
| Programmable Ac | tive Droop™ | OPTOPLANAR™ | SMART START™ | |

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